

SANCOM

SA-PAN077085-P45

7.7-8.5 GHz High Power GaN-HEMT

Features

Frequency Range: 7.7-8.5 GHz

 $P_{\text{sat}} \geq 45 \text{ dBm}$ Power Gain: $\geq 9 \text{ dB}$ Efficiency: $\geq 38\%$ $Z_{\text{in}}/Z_{\text{out}} = 50 \Omega$ 

Description

Sancom Electric's GaN-HEMT SA-PAN077085-P45 offers high power, high efficiency, ease of matching and greater consistency for high power applications with 28V operation. The SA-PAN077085-P45 typically provides 45 dBm of saturated output power and 9dB of large-signal gain and can be widely used in various RF/microwave systems.

ABSOLUTE MAXIMUM RATINGS

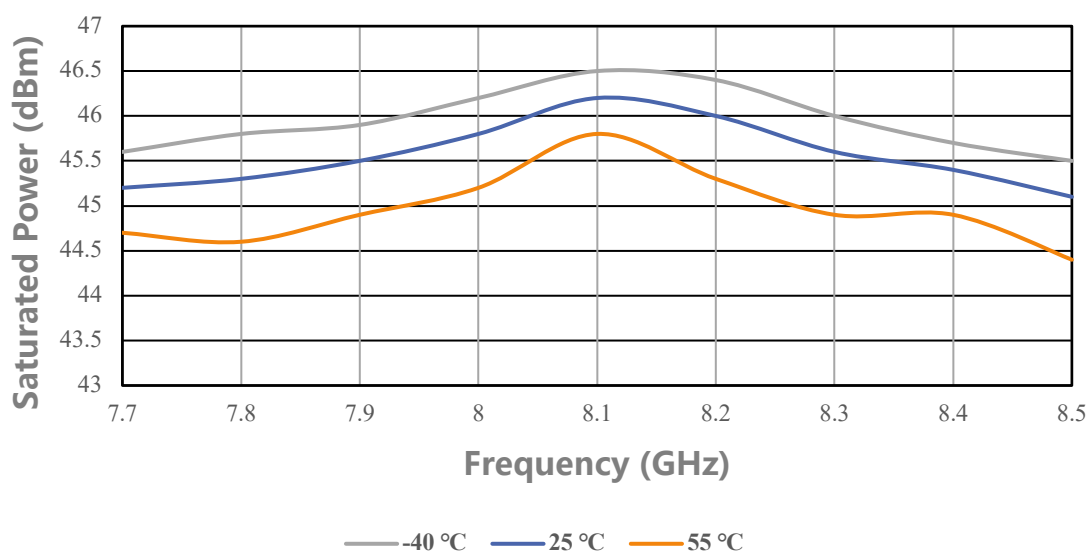
Parameter	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}	TC=25°C	40	V
Gate-Source Voltage	V_{GS}	TC=25°C	-5	V
Storage Temperature	T_{stg}	TC=25°C	-65 to 150	°C
Channel Temperature	T_{ch}	TC=25°C	150	°C

ELECTRICAL SPECIFICATIONS

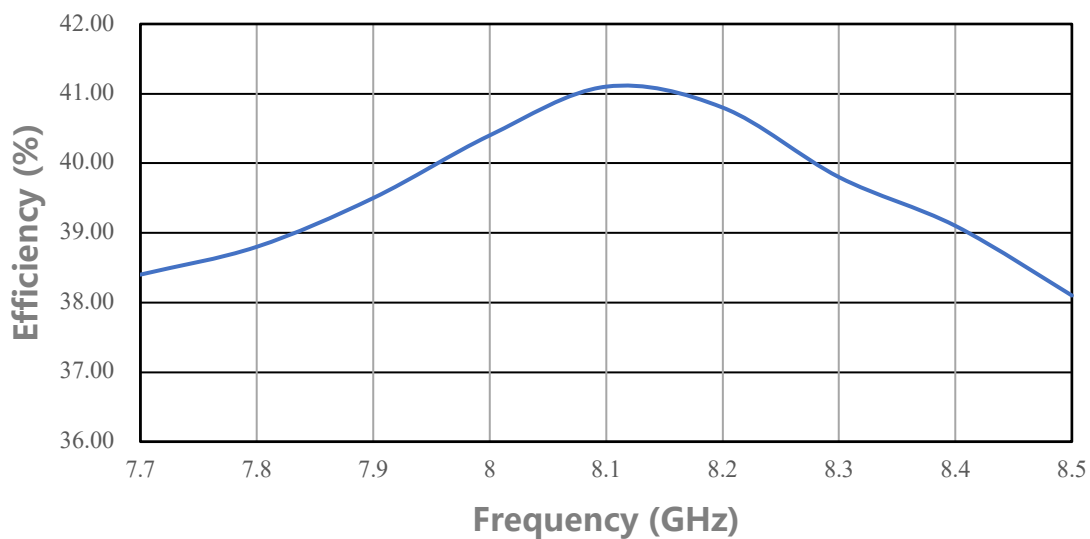
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Current	I_{DS}	V_{DS} : 28 V CW (Continuous Wave) P_{in} : 36 dBm Freq: 7.7~ 8.5GHz	-	3	-	A
Saturated Power	P_{sat}		45	-	-	dBm
Power Gain	G_p		9	-	-	dB
Efficiency	η		38	-	-	%
Flatness	ΔG		-0.8	-	0.8	dB

Performance Plots

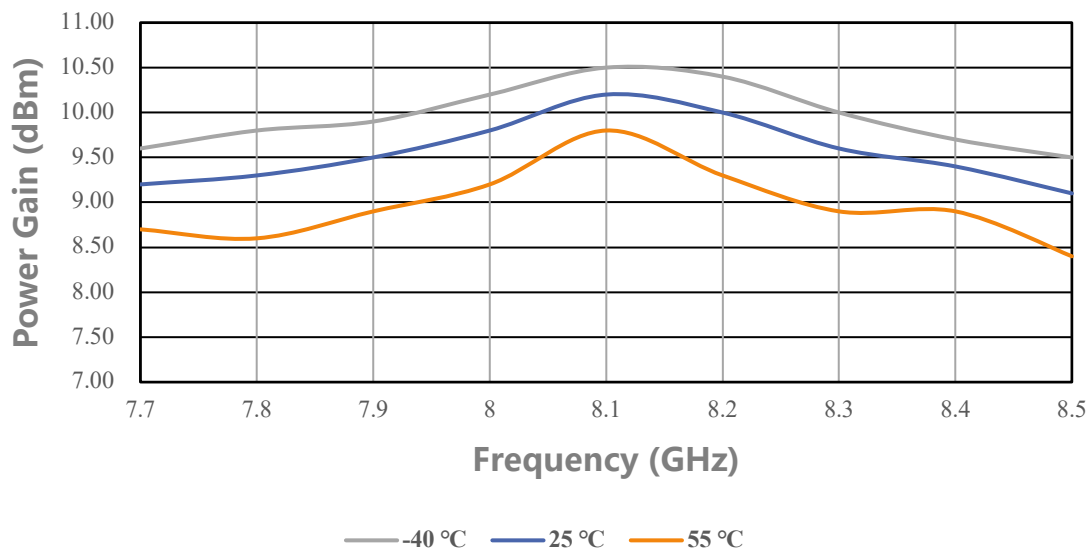
Saturated Power VS Frequency



Efficiency VS Frequency



Power Gain VS Frequency



Simplified Block Diagram



DUT information	
C1: 1 pF	Rp: 51 Ω
C2: 1000 pF	Rg: 15 Ω
C3: 100 μF	R ≈ 3.5 mm

ESD Protection

ESD	Class III	2000 V
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Outline Drawing



Unit: mm

Attention

- Please keep away from moisture during transportation and storage
- Pay attention to ESD prevention during chip use and assembly. Wear a grounding ESD bracelet.
- When adding electricity, add gate electricity first and then add leakage electricity